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IPI90R800C3

## CoolMOS™ Power Transistor

### Features

- Lowest figure-of-merit  $R_{ON} \times Q_g$
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Ultra low gate charge

### Product Summary

$V_{DS} @ T_J=25^\circ\text{C}$	900	V
$R_{DS(on),max} @ T_J=25^\circ\text{C}$	0.8	$\Omega$
$Q_{g,typ}$	42	nC

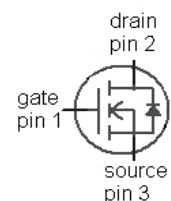
### CoolMOS™ 900V is designed for:

- Quasi Resonant Flyback / Forward topologies
- PC Silverbox and consumer applications
- Industrial SMPS

PG-TO262



Type	Package	Marking
IPI90R800C3	PG-TO262	9R800C



Maximum ratings, at  $T_J=25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25^\circ\text{C}$	6.9	A
		$T_C=100^\circ\text{C}$	4.4	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25^\circ\text{C}$	15	
Avalanche energy, single pulse	$E_{AS}$	$I_D=1.4\text{ A}, V_{DD}=50\text{ V}$	157	mJ
Avalanche energy, repetitive $t_{AR}$ <sup>2),3)</sup>	$E_{AR}$	$I_D=1.4\text{ A}, V_{DD}=50\text{ V}$	0.46	
Avalanche current, repetitive $t_{AR}$ <sup>2),3)</sup>	$I_{AR}$		1.4	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=0\dots 400\text{ V}$	50	V/ns
Gate source voltage	$V_{GS}$	static	$\pm 20$	V
		AC (f>1 Hz)	$\pm 30$	
Power dissipation	$P_{tot}$	$T_C=25^\circ\text{C}$	104	W
Operating and storage temperature	$T_J, T_{stg}$		-55 ... 150	$^\circ\text{C}$



IPI90R800C3

Maximum ratings, at  $T_J=25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	4.1	A
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$		15	
Reverse diode $dv/dt$ <sup>4)</sup>	$dv/dt$		4	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		-	-	1.2	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	lead	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	1.6 mm (0.063 in.) from case for 10 s	-	-	260	$^\circ\text{C}$

Electrical characteristics, at  $T_J=25\text{ }^\circ\text{C}$ , unless otherwise specified

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	900	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.46\text{ mA}$	2.5	3	3.5	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=900\text{ V}, V_{GS}=0\text{ V}, T_J=25\text{ }^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{DS}=900\text{ V}, V_{GS}=0\text{ V}, T_J=150\text{ }^\circ\text{C}$	-	10	-	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=4.1\text{ A}, T_J=25\text{ }^\circ\text{C}$	-	0.62	0.8	$\Omega$
		$V_{GS}=10\text{ V}, I_D=4.1\text{ A}, T_J=150\text{ }^\circ\text{C}$	-	1.7	-	
Gate resistance	$R_G$	$f=1\text{ MHz}, \text{open drain}$	-	1.3	-	$\Omega$



### IPI90R800C3

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

#### Dynamic characteristics

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	1100	-	pF
Output capacitance	$C_{oss}$		-	52	-	
Effective output capacitance, energy related <sup>5)</sup>	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 500 V	-	34	-	
Effective output capacitance, time related <sup>6)</sup>	$C_{o(tr)}$		-	130	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=4.1\text{ A},$ $R_G=50\ \Omega$	-	70	-	ns
Rise time	$t_r$		-	20	-	
Turn-off delay time	$t_{d(off)}$		-	400	-	
Fall time	$t_f$		-	32	-	

#### Gate Charge Characteristics

Gate to source charge	$Q_{gs}$	$V_{DD}=400\text{ V}, I_D=4.1\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	5	-	nC
Gate to drain charge	$Q_{gd}$		-	18	-	
Gate charge total	$Q_g$		-	42	tbd	
Gate plateau voltage	$V_{plateau}$		-	4.6	-	V

#### Reverse Diode

Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=4.1\text{ A},$ $T_J=25\text{ }^\circ\text{C}$	-	0.8	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	360	-	ns
Reverse recovery charge	$Q_{rr}$		-	5.3	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	24	-	A

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{J,max}$

<sup>3)</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV}=E_{AR} \cdot f$ .

<sup>4)</sup>  $I_{SD} \leq I_D$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DClink}=400\text{ V}$ ,  $V_{peak} < V_{(BR)DSS}$ ,  $T_J < T_{J,max}$ , identical low side and high side switch

<sup>5)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 50%  $V_{DSS}$ .

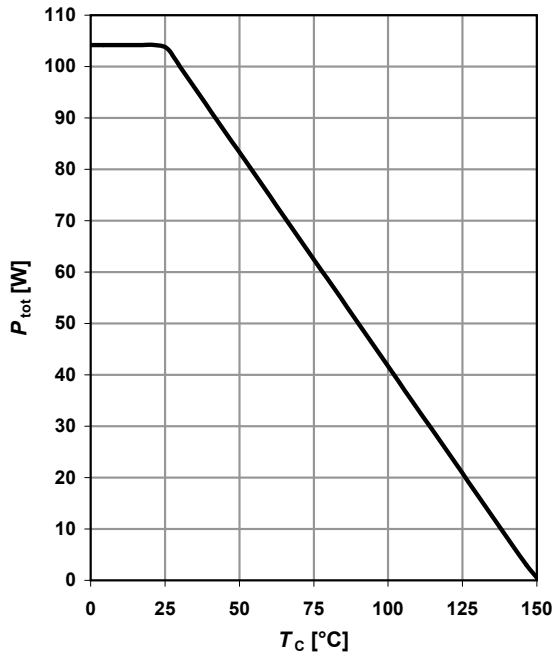
<sup>6)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 50%  $V_{DSS}$ .



**IPI90R800C3**

**1 Power dissipation**

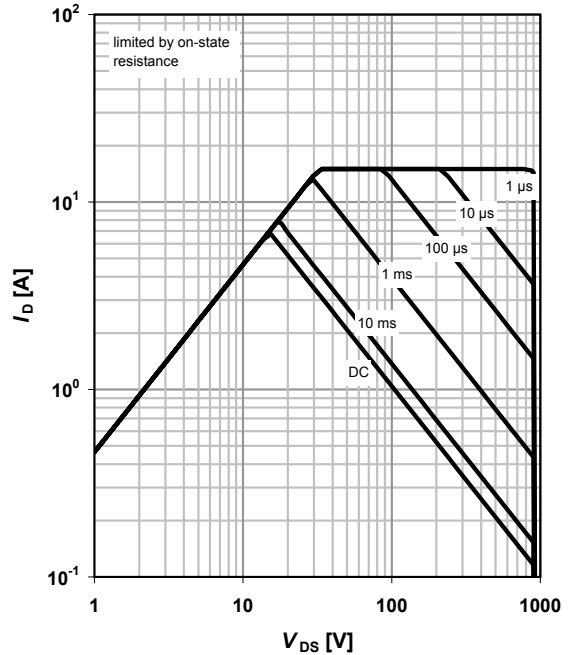
$P_{tot}=f(T_C)$



**2 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

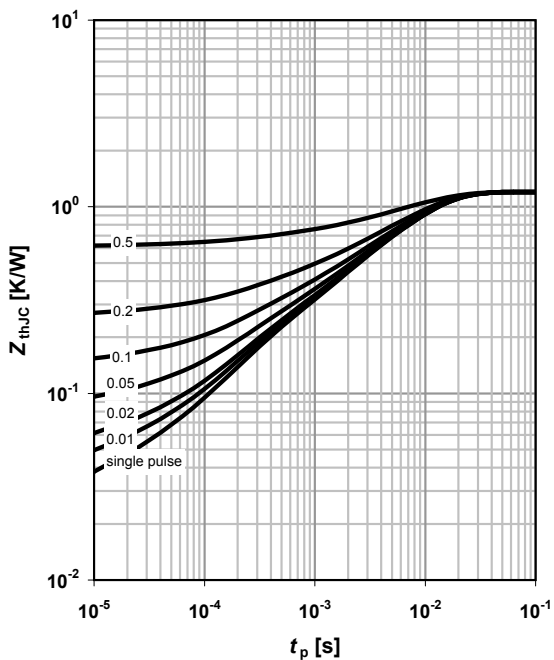
parameter:  $t_p$



**3 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

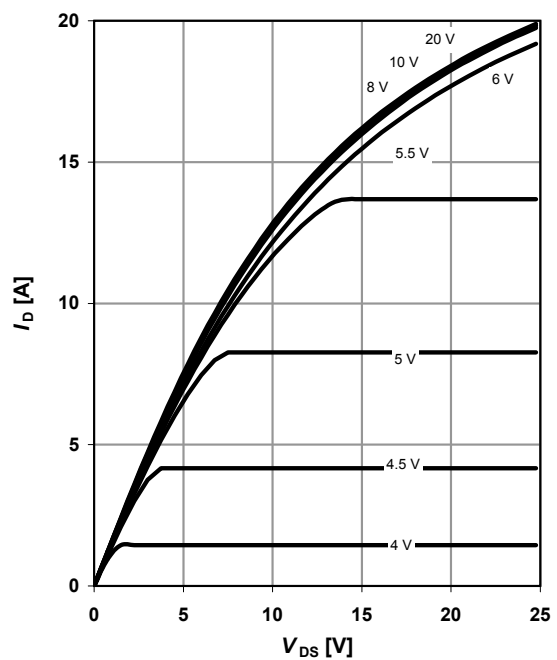
parameter:  $D=t_p/T$



**4 Typ. output characteristics**

$I_D=f(V_{DS}); T_J=25\text{ °C}$

parameter:  $V_{GS}$



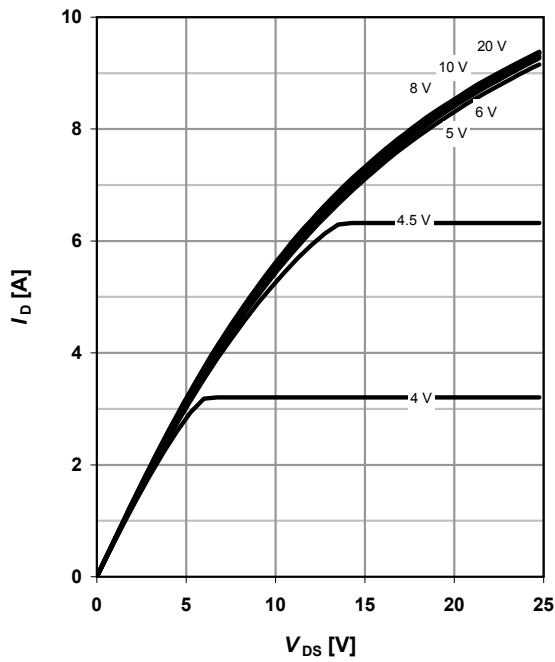


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**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_J = 150\text{ }^\circ\text{C}$

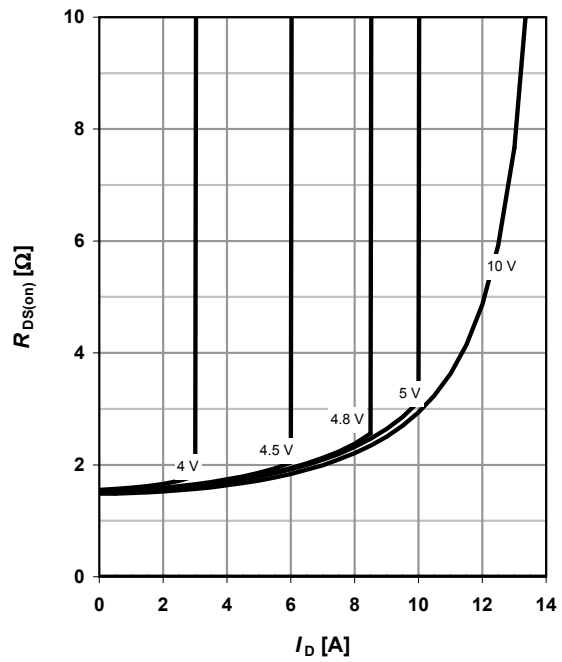
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance**

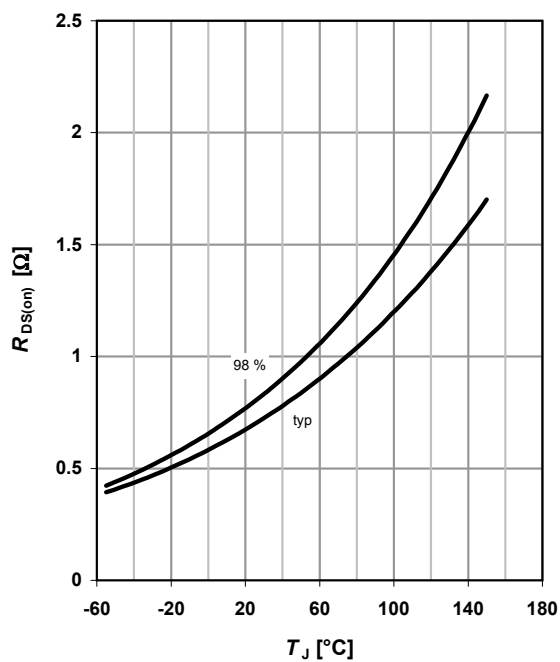
$R_{DS(on)} = f(I_D); T_J = 150\text{ }^\circ\text{C}$

parameter:  $V_{GS}$



**7 Drain-source on-state resistance**

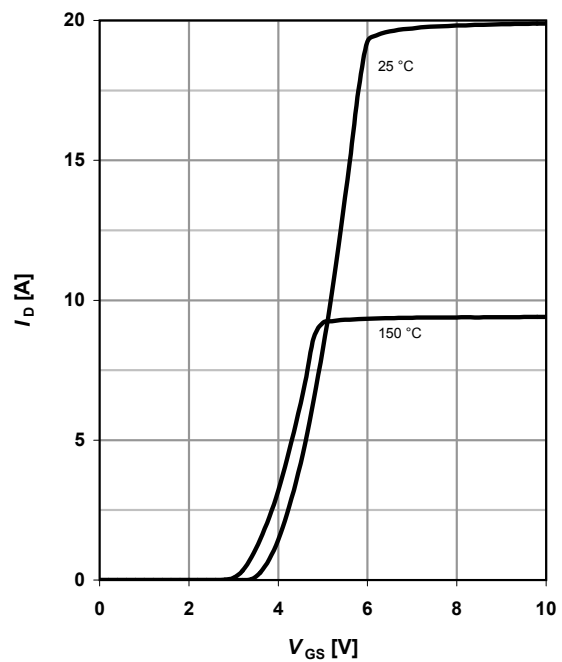
$R_{DS(on)} = f(T_J); I_D = 4.1\text{ A}; V_{GS} = 10\text{ V}$



**8 Typ. transfer characteristics**

$I_D = f(V_{GS}); V_{DS} = 20\text{ V}$

parameter:  $T_J$



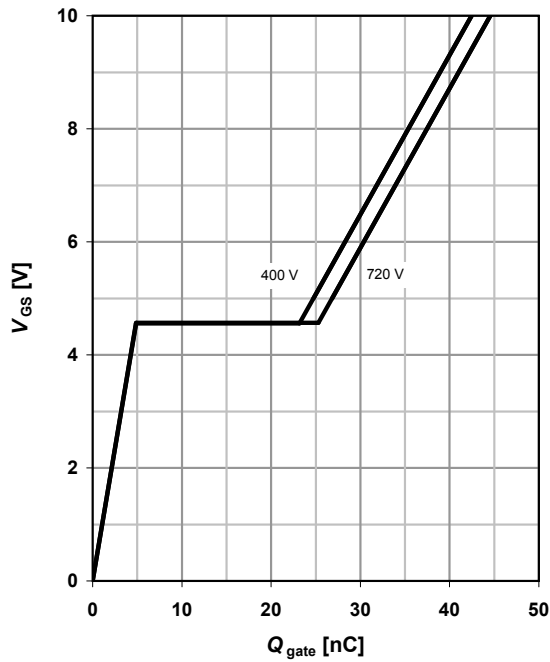


**IPI90R800C3**

**9 Typ. gate charge**

$V_{GS}=f(Q_{gate}); I_D=4.1\text{ A pulsed}$

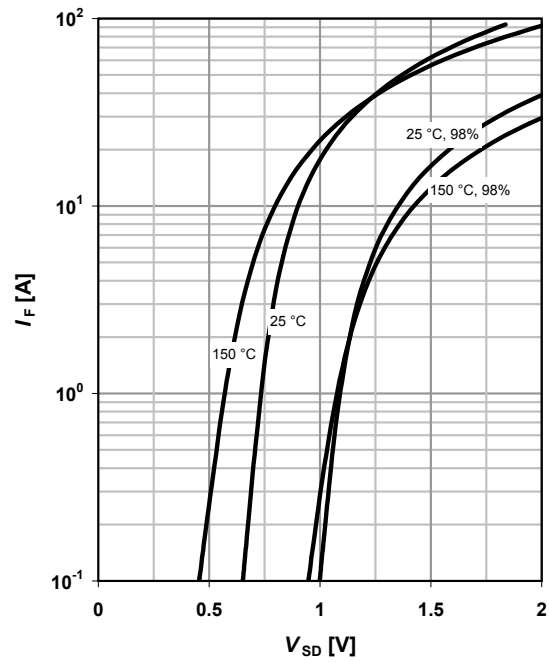
parameter:  $V_{DD}$



**10 Forward characteristics of reverse diode**

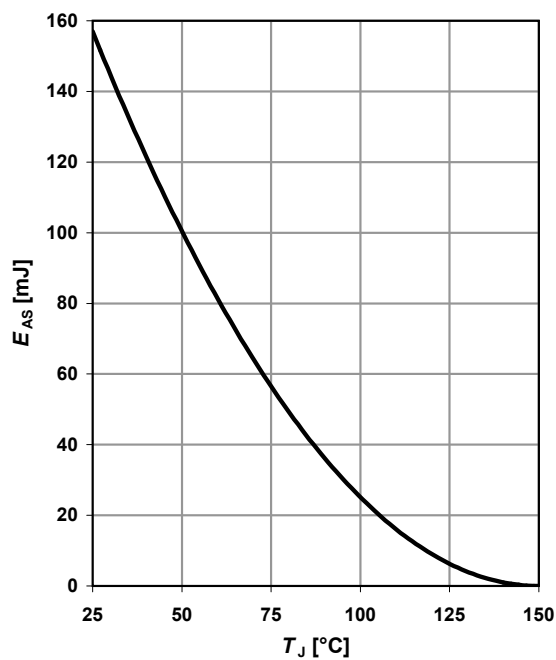
$I_F=f(V_{SD})$

parameter:  $T_J$



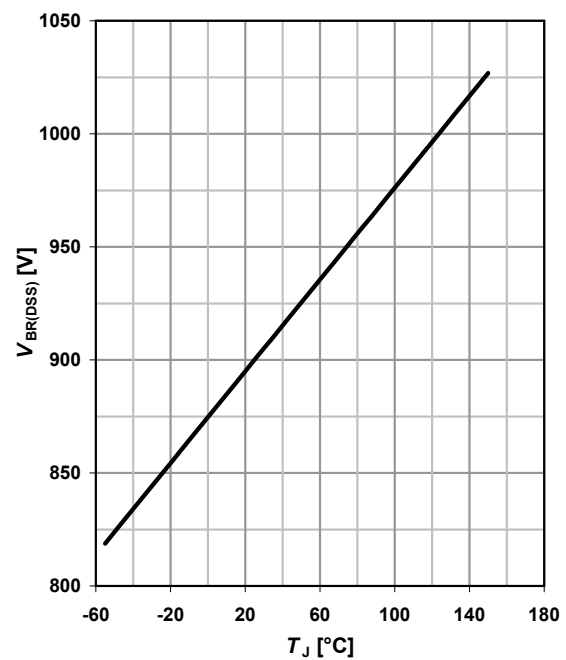
**11 Avalanche energy**

$E_{AS}=f(T_J); I_D=1.4\text{ A}; V_{DD}=50\text{ V}$



**12 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_J); I_D=0.25\text{ mA}$

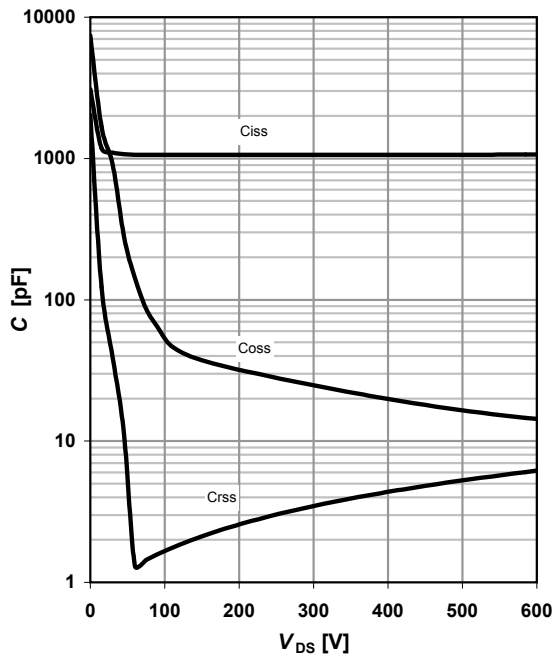




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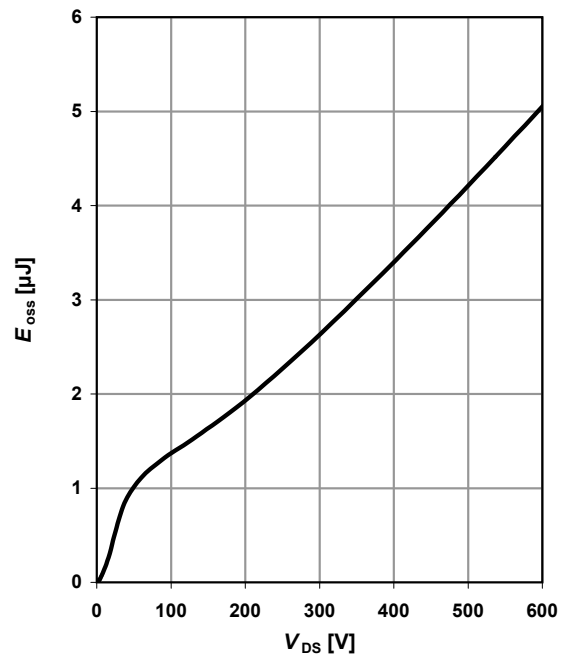
**13 Typ. capacitances**

$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**14 Typ. C<sub>oss</sub> stored energy**

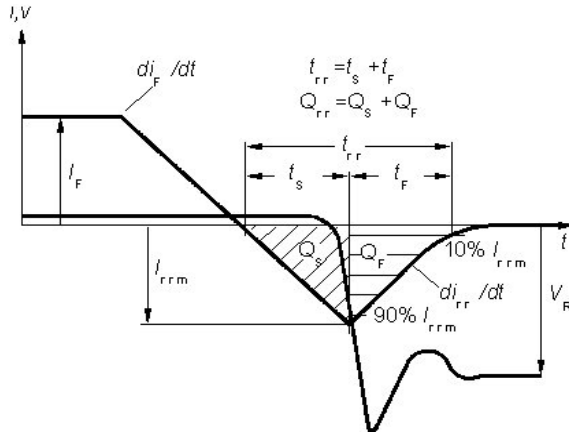
$E_{oss} = f(V_{DS})$







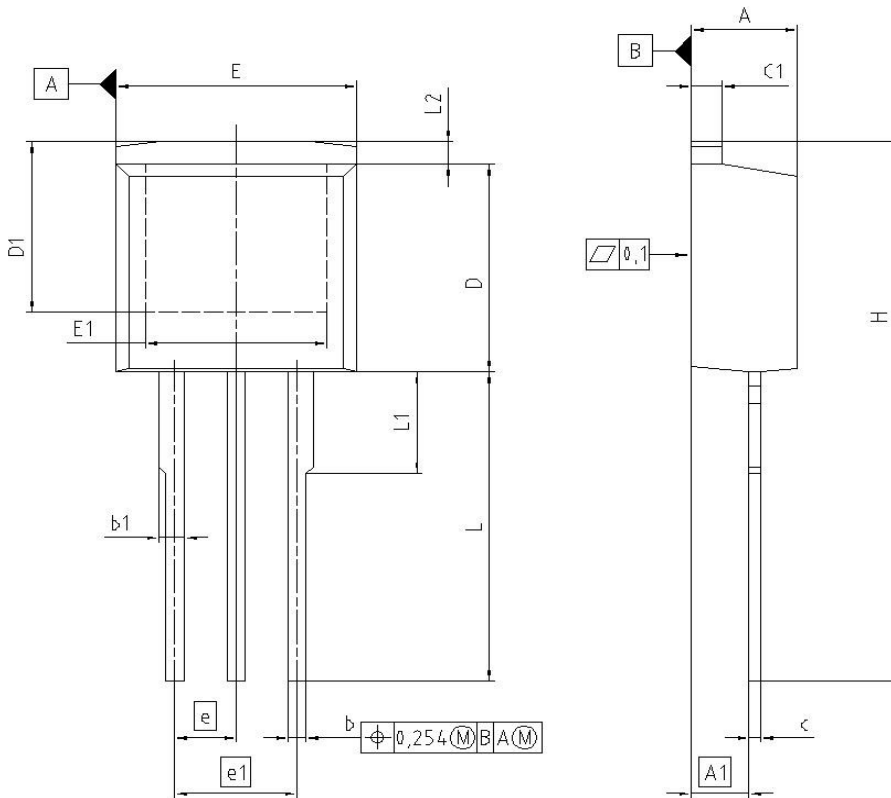
**Definition of diode switching characteristics**





**IPI90R800C3**

**PG-TO262 Outlines**



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.500	0.169	0.177
A1	2.150	2.650	0.085	0.104
b	0.650	0.850	0.026	0.033
b1	0.635	1.400	0.025	0.055
c	0.400	0.600	0.016	0.024
c1	1.170	1.370	0.046	0.054
D	9.050	9.450	0.356	0.372
D1	6.900	7.650	0.272	0.301
E	9.800	10.200	0.386	0.402
E1	7.250	8.600	0.285	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	4.350	4.750	0.171	0.187
L2	0.700	1.300	0.028	0.051

**REFERENCE**  
JEDEC TO262

**SCALE**

**EUROPEAN PROJECTION**

**ISSUE DATE**  
01-06-2005

**FILE**  
TO262\_1

Dimensions in mm/inches



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